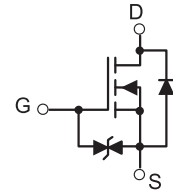




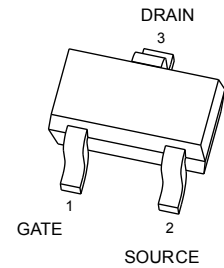
MT1012 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	700mΩ@4.5V	500mA
	850mΩ@2.5V	



FEATURE

- High-Side Switching
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- ESD protected



APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

SOT-23

Marking : A2

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GS}	± 10	
Drain Current-Continuous	$I_{D(DC)}$	500	mA
Drain Current -Pulsed(note1)	$I_{DM(pulse)}$	1000	
Power Dissipation (note 2 , $T_a=25^\circ\text{C}$)	P_D	150	mW
Maximum Power Dissipation (note 3 , $T_c=25^\circ\text{C}$)		275	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	455	
Storage Temperature	T_j	150	$^\circ\text{C}$
Junction Temperature	T_{stg}	-55 ~+150	



$T_a=25^{\circ}\text{C}$ unless otherwise specified

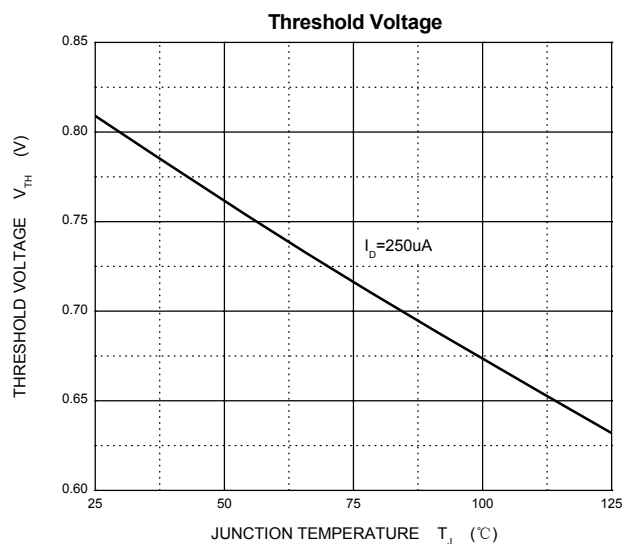
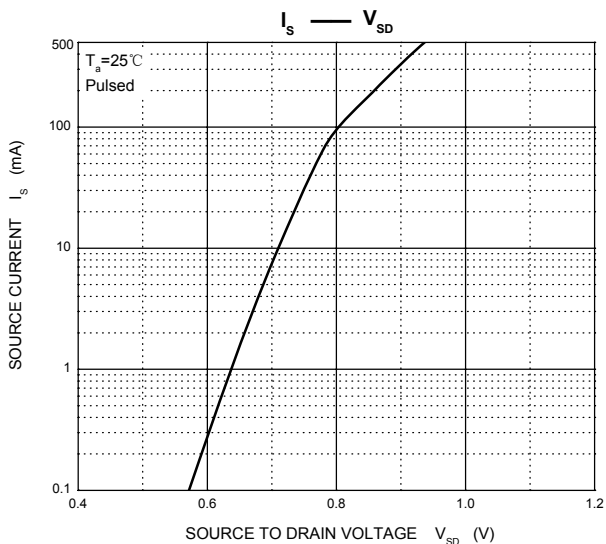
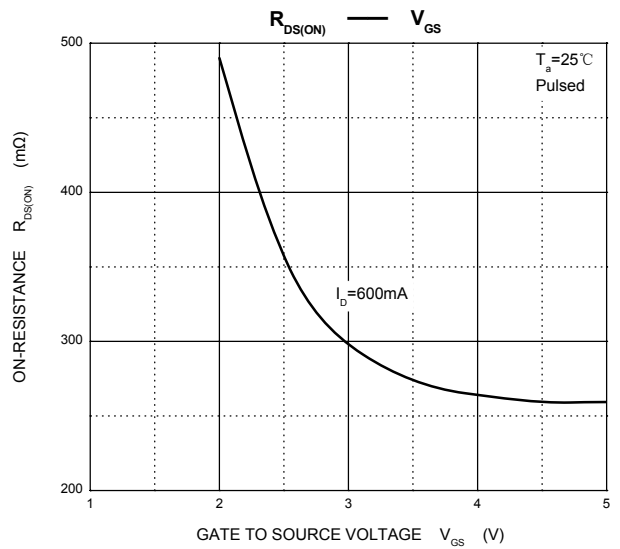
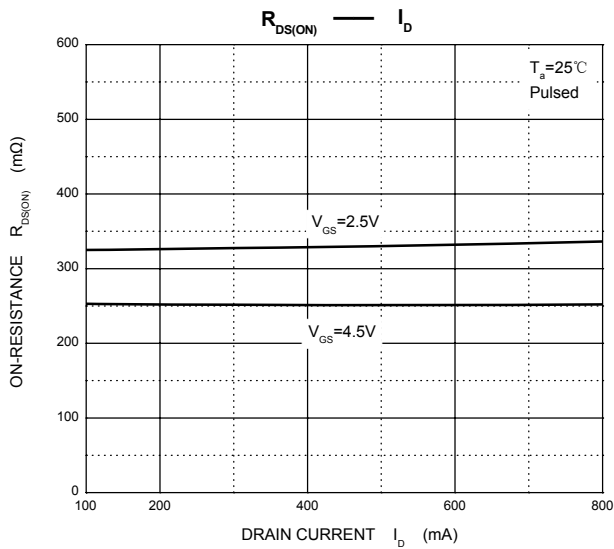
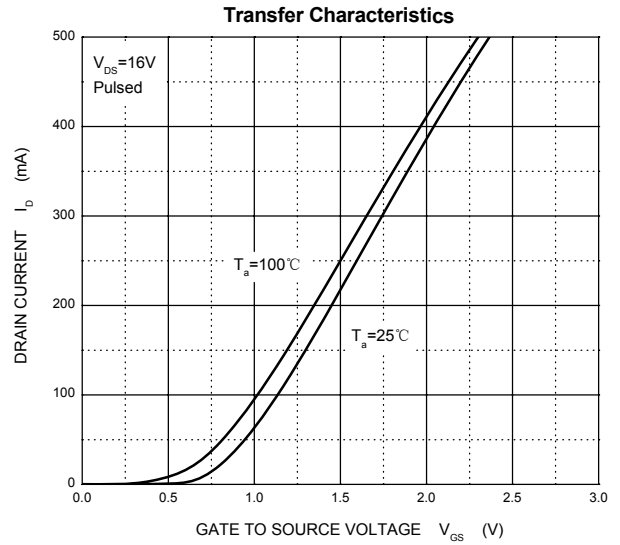
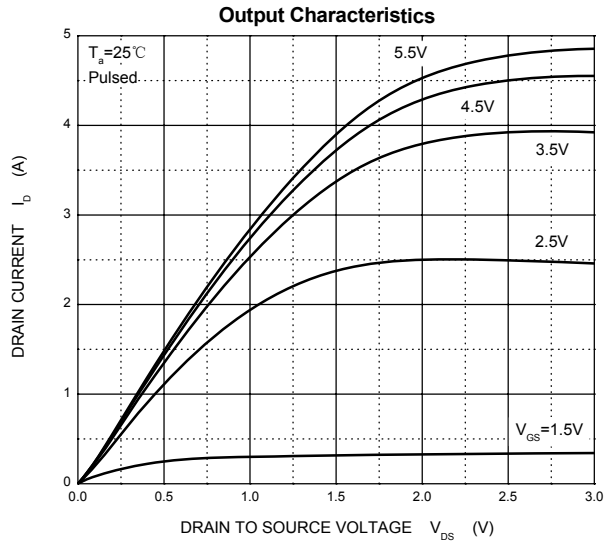
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
On/Off States						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.45	0.8	1.2	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 4.5V$			± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 600mA$		250	700	m Ω
		$V_{GS} = 2.5V, I_D = 500mA$		330	850	
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 400mA$		1		S
Dynamic Characteristics						
Input Capacitance (note 4)	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		100		pF
Output Capacitance (note 4)	C_{oss}			16		
Reverse Transfer Capacitance (note 4)	C_{rss}			12		
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 250mA$		750		nC
Gate-Source Charge	Q_{gs}			75		
Gate-Drain Charge	Q_{gd}			225		
Switching Times (note 4)						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, R_L = 47\Omega, I_D = 200mA, V_{GS} = 4.5V, R_G = 10\Omega$		5		nS
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall Time	t_f			11		
Drain-Source Diode Characteristics						
Drain-Source Diode Forward Voltage (note 5)	V_{SD}	$I_S = 0.15A, V_{GS} = 0V$			1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_a=25^{\circ}\text{C}$.
3. This test is performed with infinite heat sink at $T_c=25^{\circ}\text{C}$.
4. These parameters have no way to verify.
5. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.



Typical Characteristics

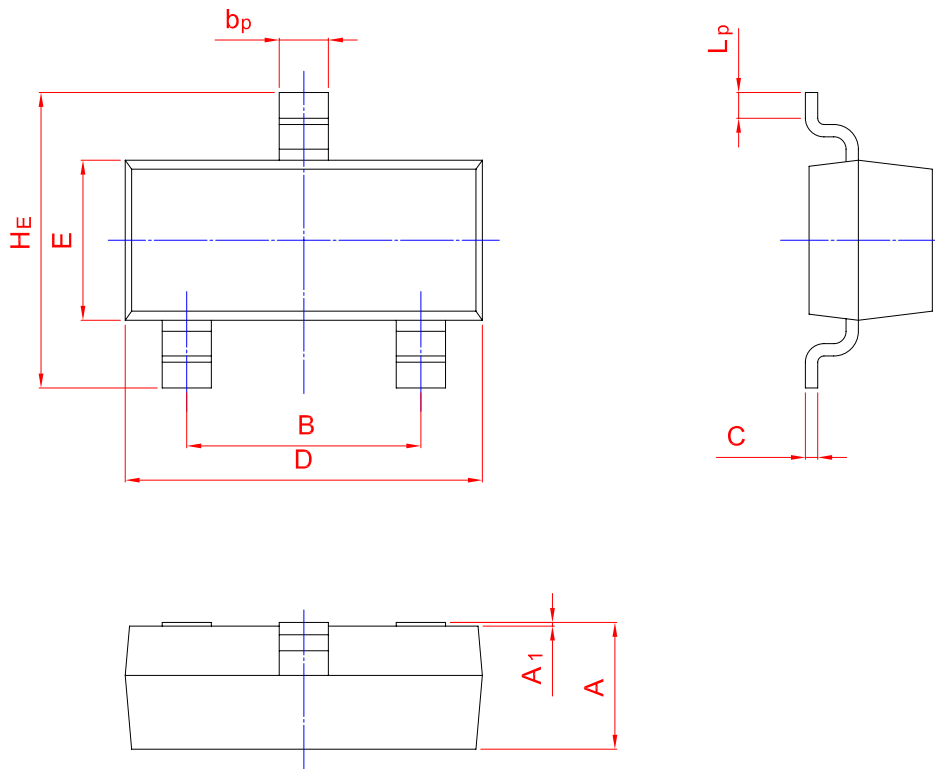
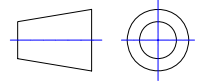




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20